

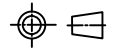

Note:

1. SUBSTRATE:IR MONO GRADE SI
2. GROWING METHOD:CZ
3. CLEAR APERTURE:95%
4. SURFACE QUALITY:S1&S2 60-40 SCRATCH-DIG
5. PARALLELISM:3ARCMIN
6. POWER:5 λ/2
7. IRREGULARITY:3 λ/2
8. COATING: NONE

9 FINE GRIND SURFACE

SPECIFICATIONS SUBJECT TO CHANGE WITHOUT NOTICE

FOR INFORMATION ONLY NOT FOR MANUFACTURE

DRAWING PROJECTION 		ALL DIMS IN	MM
DESIGNED	CHECKED	APPROVED	SCALE
			1:1
MATERIAL	Silicon	TITLE	SI IR-MONO ROUND WINDOW Ø50*T3
 本征晶体 INTRINSIC CRYSTAL	www.icc-mall.com	DWG NO	PSI01E020
		EDITION	1ST SHEET 1/1